

Silicon PNP Power Transistors

2SA1062

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC2486
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |

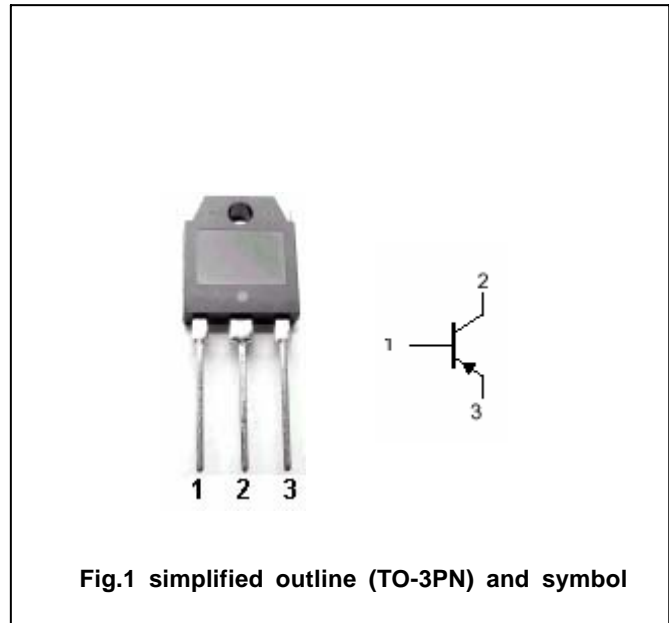


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | -120 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -120 | V |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current (DC) | | -7 | A |
| I_{CM} | Collector current-peak | | -12 | A |
| P_C | Collector power dissipation | $T_C=25^\circ\text{C}$ | 80 | W |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-10mA ; I _B =0 | -120 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-5A ; I _B =-0.5A | | | -2.0 | V |
| V _{BE} | Base-emitter on voltage | I _C =-5A ; V _{CE} =-5V | | | -1.8 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-120V ; I _E =0 | | | -50 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =-3V ; I _C =0 | | | -50 | μ A |
| h _{FE-1} | DC current gain | I _C =-20mA ; V _{CE} =-5V | 20 | | | |
| h _{FE-2} | DC current gain | I _C =-1A ; V _{CE} =-5V | 40 | | 200 | |
| h _{FE-3} | DC current gain | I _C =-5A ; V _{CE} =-5V | 20 | | | |
| f _T | Transition frequency | I _C =-0.5A ; V _{CE} =-5V | | 20 | | MHz |

◆ h_{FE-2} Classifications

| R | Q | P |
|-------|--------|---------|
| 40-80 | 60-120 | 100-200 |

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PACKAGE OUTLINE

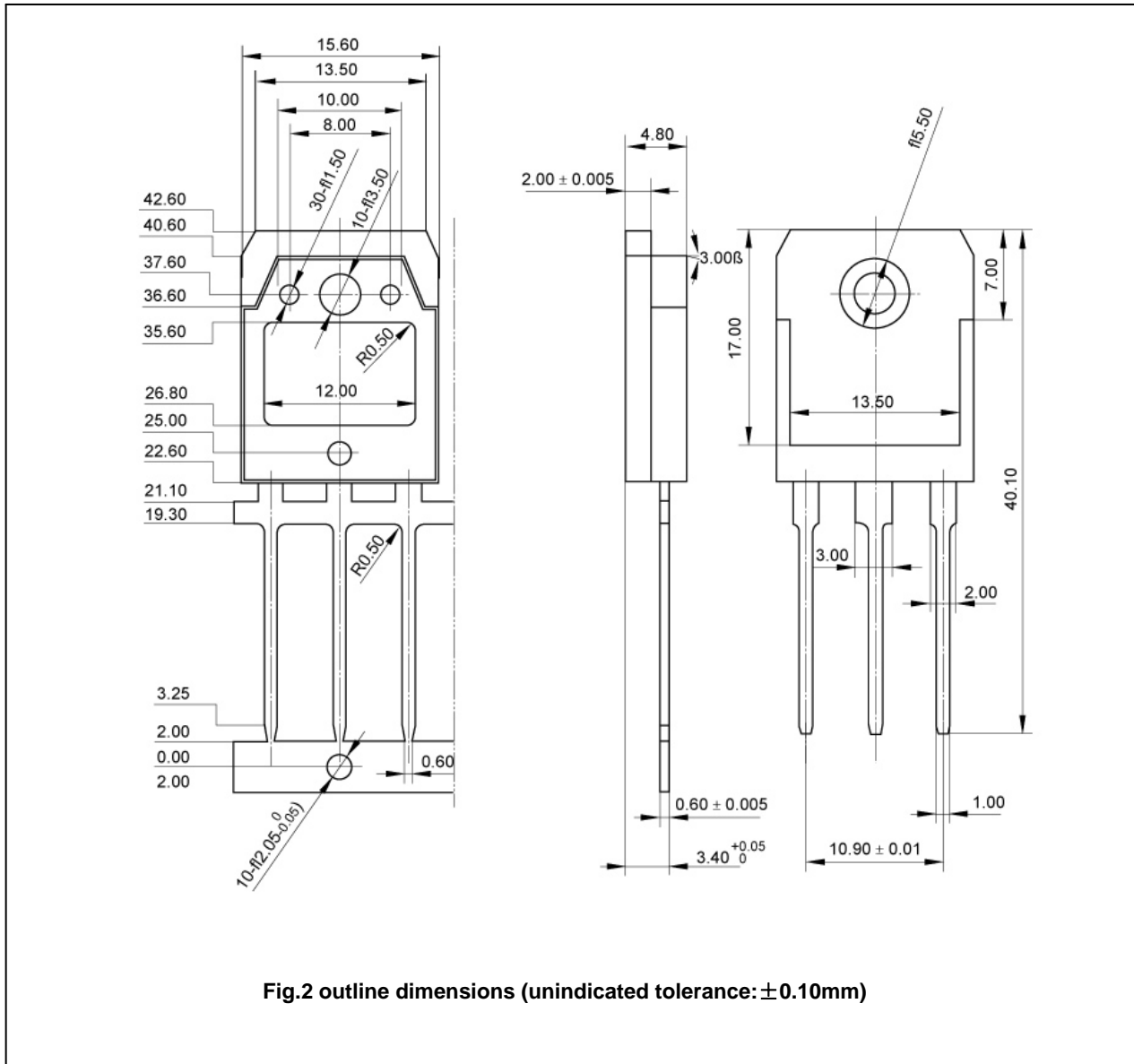


Fig.2 outline dimensions (unindicated tolerance: ±0.10mm)